

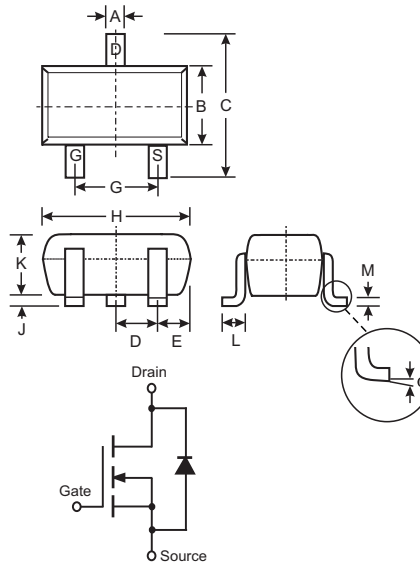
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Lead Free/RoHS Compliant (Note 4)**
- **"Green" Device (Note 5 and 6)**

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 6. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Code (See Page 2): K38
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)



SOT-323		
Dim	Min	Max
A	0.25	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.18
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	BSS138W	Units
Drain-Source Voltage	V_{DS}	50	V
Drain-Gate Voltage (Note 1)	V_{DGR}	50	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current (Note 2)	I_D	200	mA
Total Power Dissipation (Note 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	75	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 50V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	0.5	1.2	1.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS (ON)}	—	1.4	3.5	Ω	V _{GS} = 10V, I _D = 0.22A
Forward Transconductance	g _{FS}	100	—	—	mS	V _{DS} =25V, I _D = 0.2A, f = 1.0KHz
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	50	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{Oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{Rss}	—	—	8.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	—	20	ns	V _{DD} = 30V, I _D = 0.2A, R _{GEN} = 50Ω
Turn-Off Delay Time	t _{D(OFF)}	—	—	20	ns	

- Note:
1. $R_{GS} \leq 20K\Omega$.
 2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 3. Short duration test pulse used to minimize self-heating effect.
 4. No purposefully added lead.

Ordering Information (Note 5 & 7)

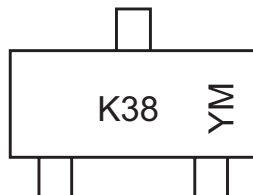
Device	Packaging	Shipping
BSS138W-7-F	SOT-323	3000/Tape & Reel

Notes: 5. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

6. Product manufactured with Date Code 0609 (week 9, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0609 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

7. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



K38 = Product Type Marking Code

YM = Date Code Marking

Y = Year ex: N = 2002

M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

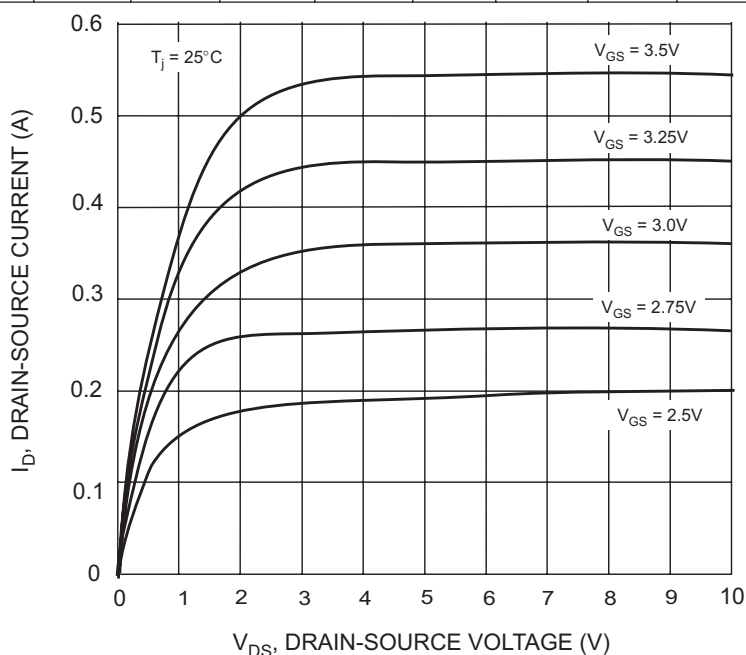


Fig. 1 Drain-Source Current vs. Drain-Source Voltage

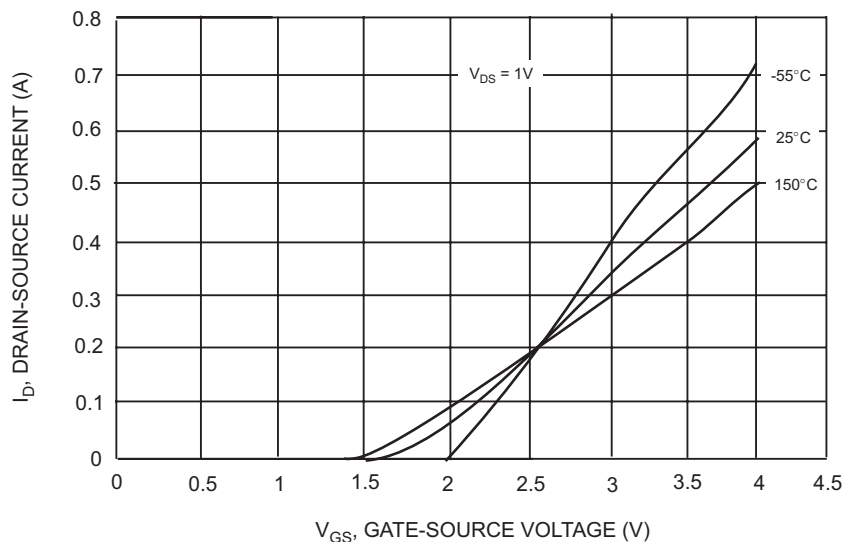


Fig. 2 Transfer Characteristics

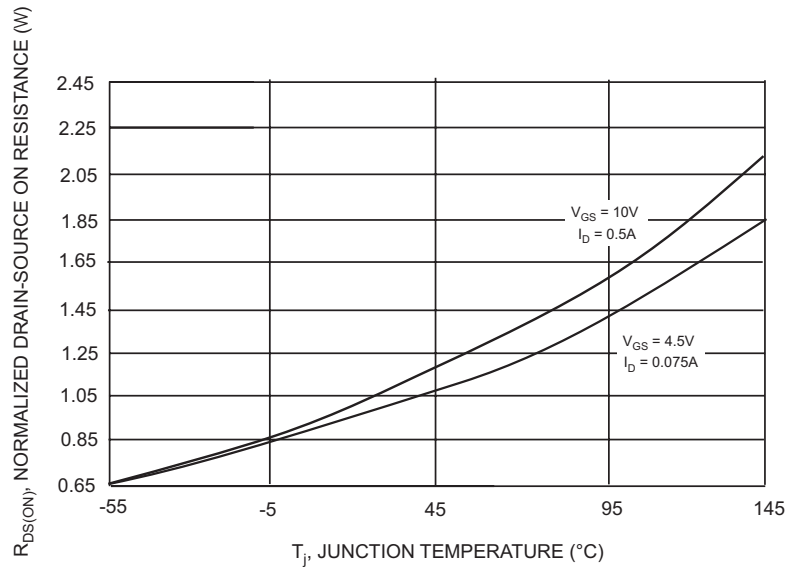


Fig. 3 Drain-Source On Resistance vs. Junction Temperature

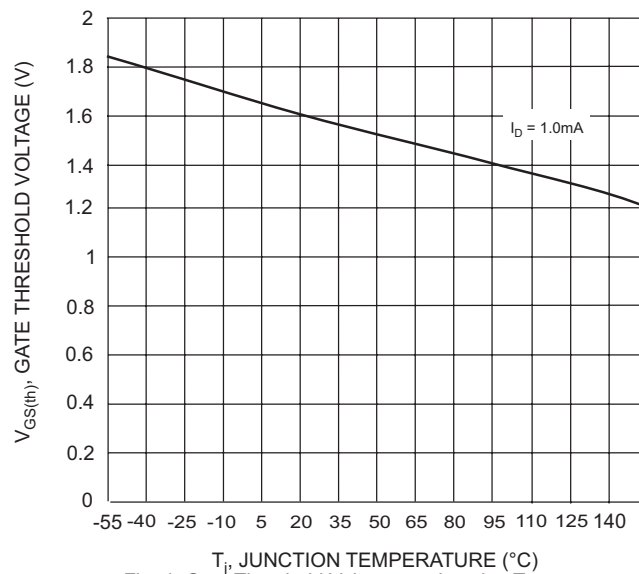


Fig. 4 Gate Threshold Voltage vs. Junction Temperature

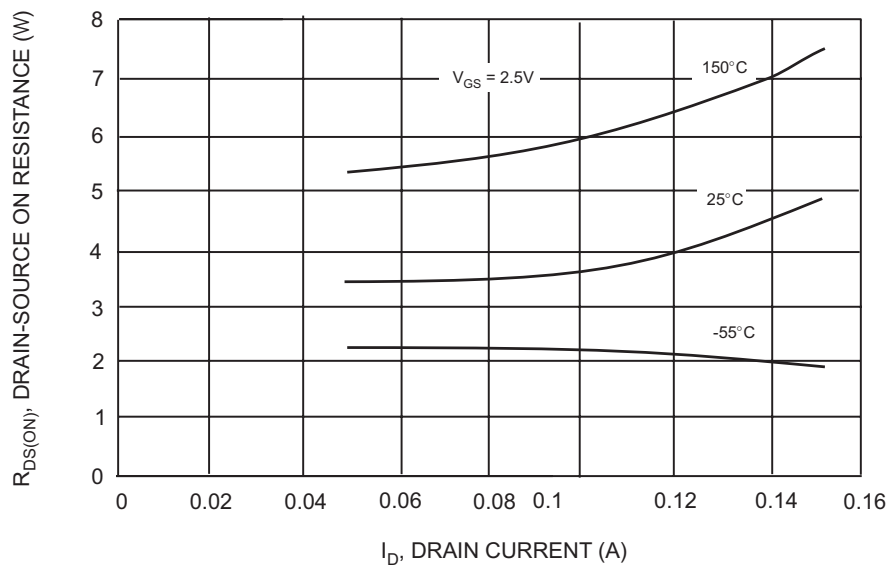


Fig. 5 Drain-Source On Resistance vs. Drain Current

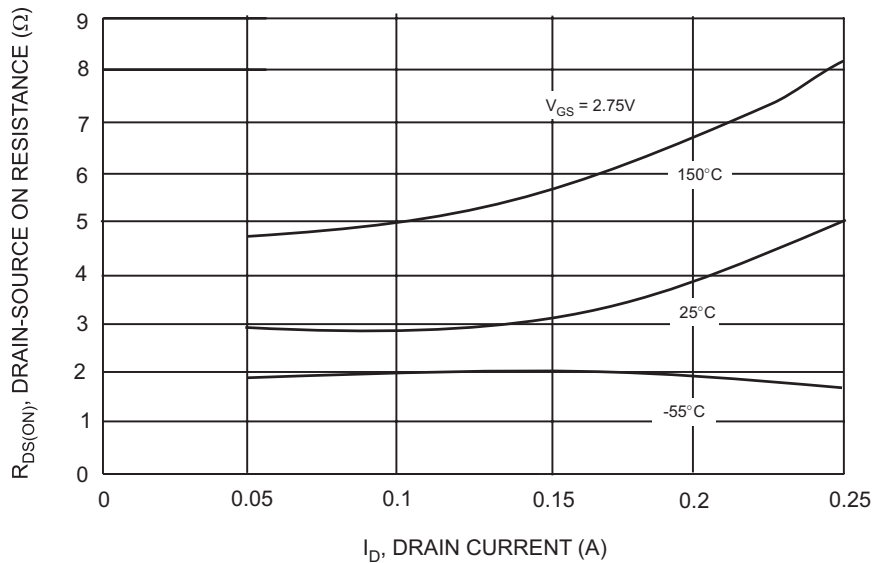


Fig. 6 Drain-Source On Resistance vs. Drain Current

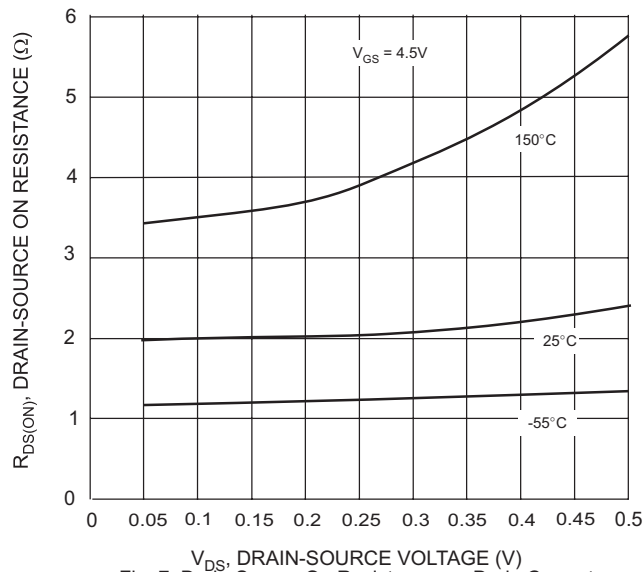


Fig. 7 Drain-Source On Resistance vs. Drain Current

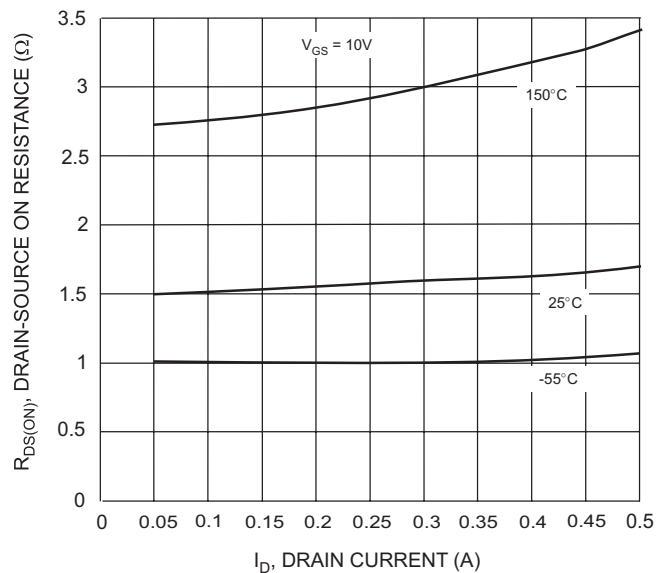


Fig. 8 Drain-Source On Resistance vs. Drain Current

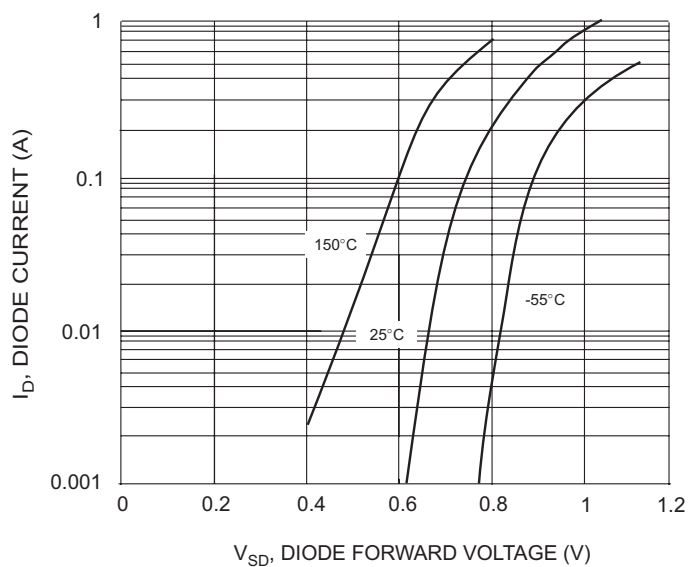


Fig. 9 Body Diode Current vs. Body Diode Voltage

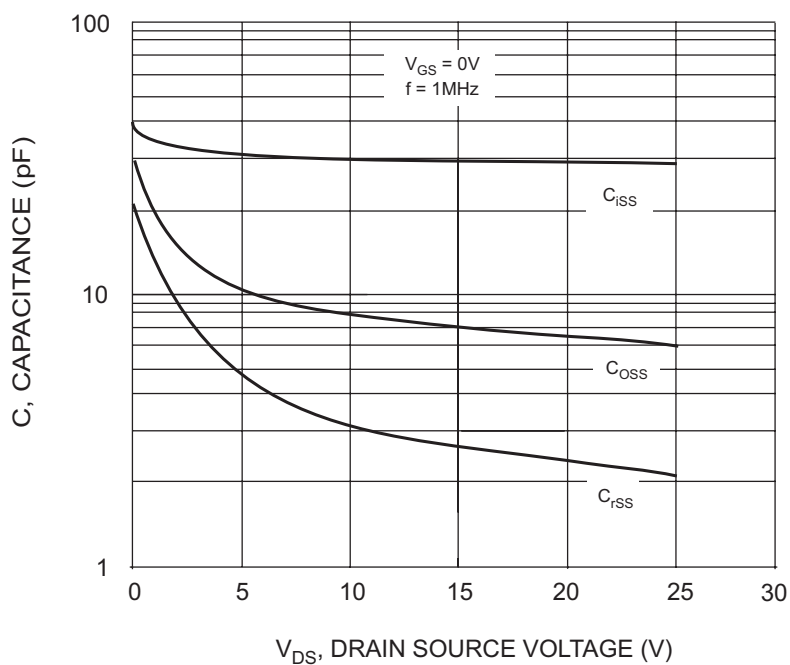


Fig. 10 Capacitance vs. Drain Source Voltage

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